

IN THE SPECIFICATION:

Please amend paragraph [0029] as follows:

Therefore, as described above, this aspect of the invention provides a chlorine-based etch process for TiN in trenches, which provides high selectivity to both silicon (including n-doped polysilicon) and dielectric mask materials (e.g. silicon nitride, silicon dioxide). The etch process uses low DC bias to provide selectivity to the mask material. Typical operating ranges are 1- 50 mT pressure, 50-5000 W decoupled source power, less than 100W bias power to the wafer. The reactive gas feedstocks contain less than 5% fluorine based halogens (e.g. CF₄, SF₆, NF₃, CF₄, SF₆, NF₃, etc.), and the balance Cl₂ (Cl₂, BCl₃-C_{l₂} (C_{l₂}, BCl₃), HCl) or Br (HBr, Br₂ Br₂) based reactants. Diluent gases may additionally be added in any range from 0% to 90% of the total feed, and can include He, Ar, N₂, Kr, etc.